

Product Overview

N25S830HA: Serial SRAM Memory, 256-kb, 3.0 V

For complete documentation, see the data sheet.

The ON Semiconductor serial SRAM family includes several integrated memory devices including this 256 kb serially accessed Static Random Access Memory, internally organized as 32 k words by 8 bits. The devices are designed and fabricated using advanced CMOS technology to provide both high-speed performance and low power. The devices operate with a single chip select (CS) input and use a simple Serial Peripheral Interface (SPI) serial bus. A single data in and data out line is used along with a clock to access data within the devices. The N25S830HA devices include a HOLD pin that allows communication to the device to be paused. While paused, input transitions will be ignored. The devices can operate over a wide temperature range of -40°C to +85°C and can be available in several standard package offerings.

Features

- 2.7 to 3.6 V power supply range
- Very low standby current - typical I_{sb} as low as 1 μ A
- Very low operating current - as low as 3 mA
- Simple memory control: single chip select (CS), serial input (SI) and serial output (SO)
- Flexible operating modes: word read and write, page mode (32 word page), and burst mode (full array)
- 32 K x 8 bit organization
- Self timed write cycles
- Built-in write protection (CS high)
- HOLD pin for pausing communication

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Type	Density	Organization (bits)	f_{cycle} Max (MHz)	V_{CC} Min (V)	V_{CC} Max (V)	$I_{standby}$ Typ (μ A)	Package Type
N25S830HAS22I	1.0666	Pb-free Halide free non AEC-Q and PPAP	Active	Serial	256 kb	32k x 8	20	2.7	3.6	1	SOIC-8
N25S830HAT22I	1.0666	Pb-free Halide free non AEC-Q and PPAP	Active	Serial	256 kb	32k x 8	20	2.7	3.6	1	TSSOP-8

For more information please contact your local sales support at www.onsemi.com.

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